



SANYO Semiconductors

DATA SHEET

2SB1121 / 2SD1621 — PNP / NPN Epitaxial Planar Silicon Transistors High-Current Driver Applications

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- Adoption of FBET, MBIT processes.
- Low collector-to-emitter saturation voltage.
- Large current capacity and wide ASO.
- Fast switching speed.
- Ultrasmall size making it easy to provide high-density, small-sized hybrid IC's.

Specifications () : 2SB1121

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)30	V
Collector-to-Emitter Voltage	VCEO		(-)25	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)2	A
Collector Current (Pulse)	ICP		(-)5	A
Collector Dissipation	PC		500	mW
		Mounted on a ceramic board (250mm ² ×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Marking 2SB1121 : BD

2SD1621 : DD

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Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)20V, I_E=0A$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0A$			(-)0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=(-)2V, I_C=(-)100mA$	100*		560*	
	h_{FE2}	$V_{CE}=(-)2V, I_C=(-)1.5A$	65			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)50mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		(32)19		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA$		(-0.35)0.18	(-0.6)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA$		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-)30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)25			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0A$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		(60)60		ns
Storage Time	t_{stg}	See specified Test Circuit.		(350)550		ns
Fall Time	t_f	See specified Test Circuit.		(25)25		ns

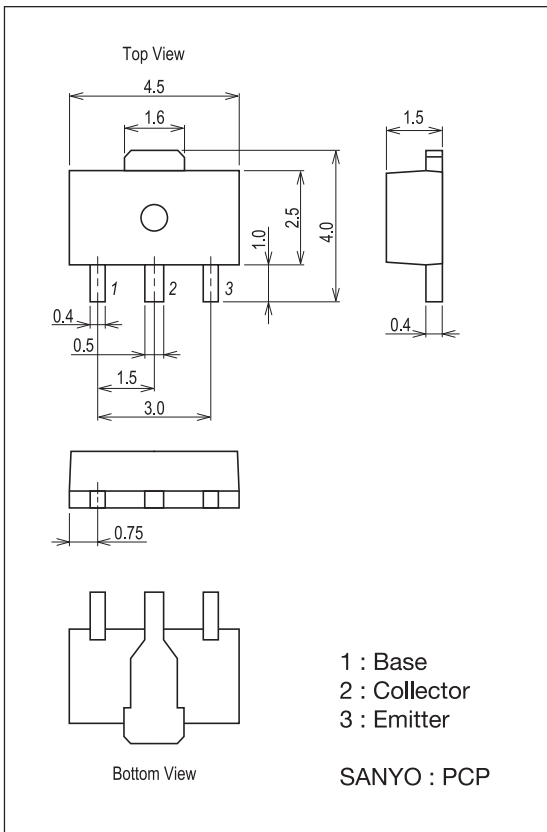
*: The 2SB1121 / 2SD1621 are classified by 100mA h_{FE} as follows:

Rank	R	S	T	U
h_{FE}	100 to 200	140 to 280	200 to 400	280 to 560

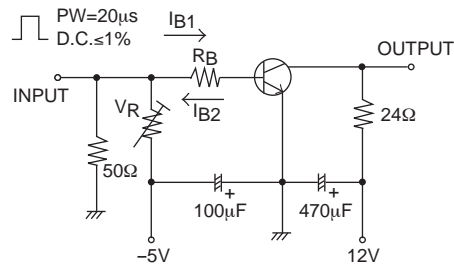
Package Dimensions

unit : mm (typ)

7007B-004

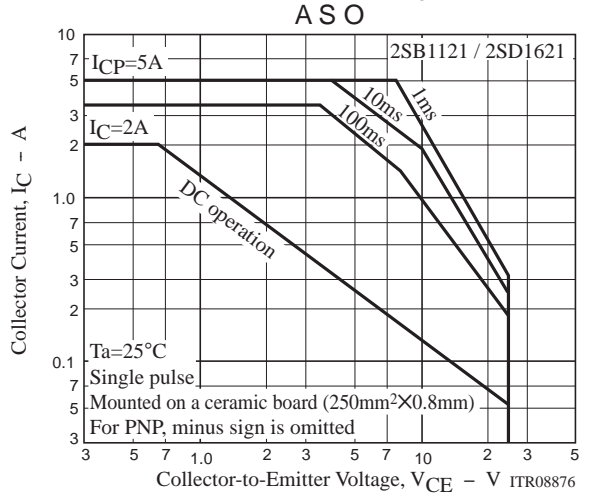
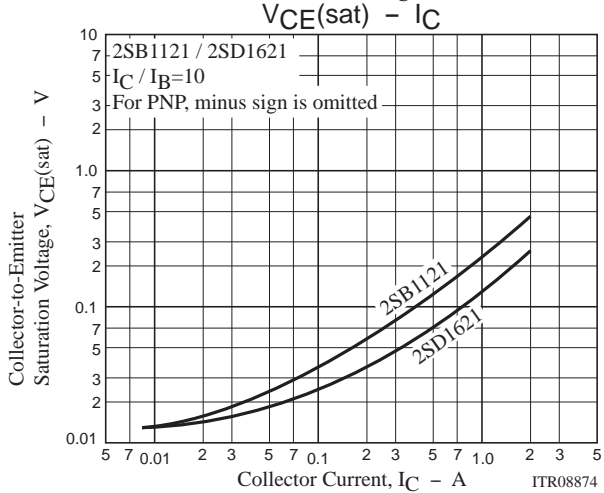
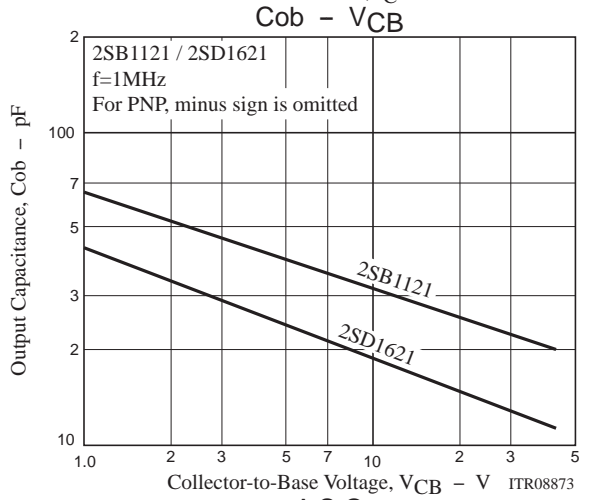
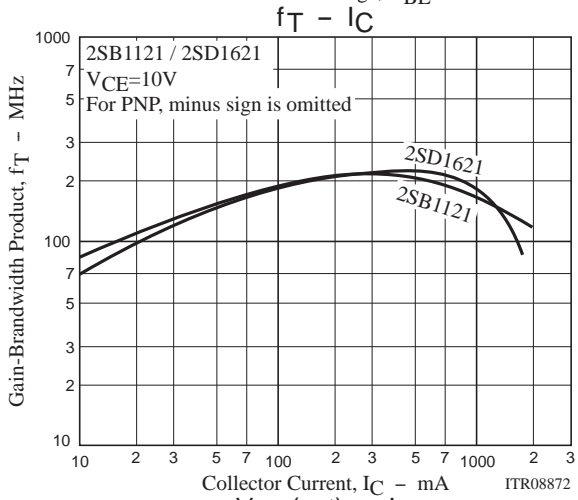
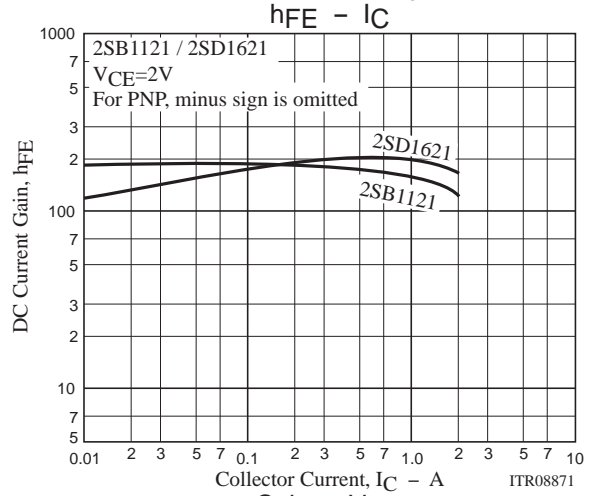
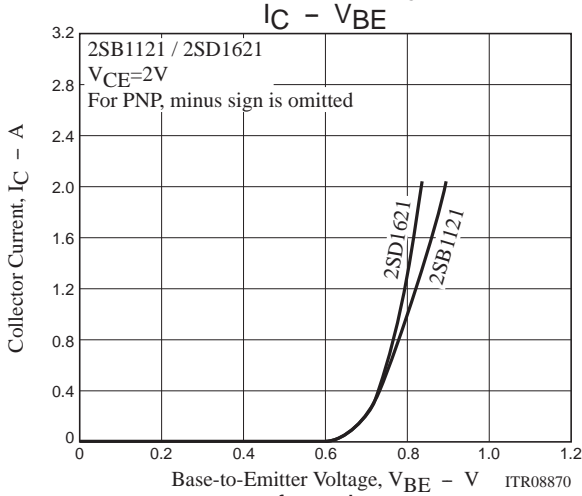
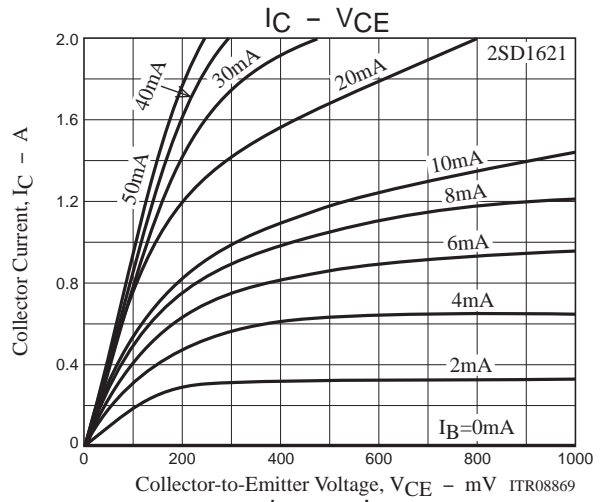
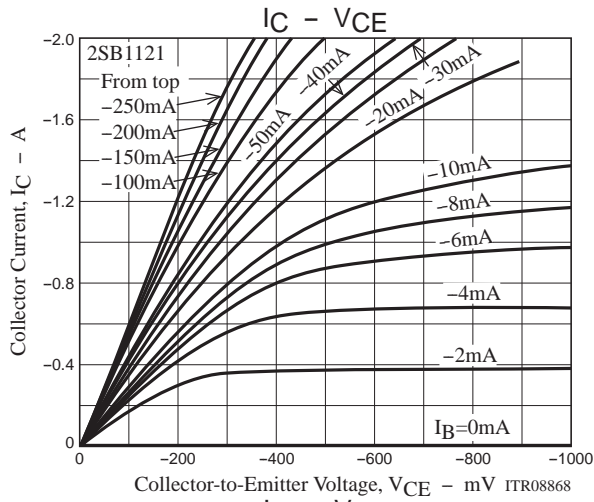


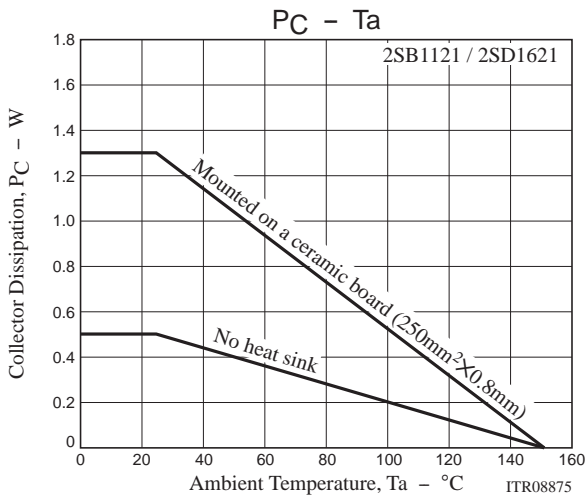
Switching Time Test Circuit



$I_C=20I_{B1} = -20I_{B2}=500mA$
(For PNP, the polarity is reversed)

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